FORM PTO-1449 (MODIFIED)	ATTY DOCKET NO.	SERIAL NO.		
LIST OF PATENTS AND PUBLICATIONS	67,200-377	Filed Herewith		
FOR APPLICANT'S INFORMATION DISCLOSURE STATEMENT	APPLICANT Fu-Liang Yang			
(Use several sheets if necessary)	FILING DATE Filed Herewith	GROUP Unknown		

REFERENCE DESIGNATION U.S. PATENT DOCUMENTS									
EXAMINER INITIAL		DOCUMENT NO.	DATE	NAME	CLASS	SUB CLASS	FILING DATE		
OF	AA_	5,023,671	Jun/1991	DiVincenzo et al		<u> </u>			
of	AB	5,119,151	Jun/1992	Onda					
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**FOREIGN PATENT DOCUMENTS** TRANSLATION SUB **EXAMINER DOCUMENT** YES/NO **CLASS** INITIAL DATE COUNTRY **CLASS** NO.\ ΑK ALAM AN

OTHER ART (including Author, Title, Date, pertinent pages, etc.)

AO Sallagoity et al, "Analysis of Width Edge Effects in Advanced Isolation Schemes for Deep Submicron CMOS Technologies", IEEE Trans. on Electron Devices, 44(11), Nov. 1996, pp. 1900-05.

AP Matsuda et al, "Novel Corner Rounding Process for Shallow Trench Isolation Utilizing MSTS (Micro-Structure Transformation of silicon). IEEE IEDM98, pp. 137-40.

EXAMINER DATE CONSIDERED 8/20/65

EXAMINER: Initial if reference considered, whether or not citation is in conformance with MPEP 609; Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to application.